

Search Hist. (7 pp.) ~~7~~... (03/18/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2631	((257/52) or (257/57) or (257/66) or (257/72)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/18 17:02
L2	237	I1 and contact adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 17:03
S1	3	"749273".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 09:07
S2	167	((257/624) or (257/625)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/17 09:19
S3	1402	((257/327) or (257/382) or (257/383) or (257/384)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/18 17:02
S4	315	S3 and contact adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 17:03
S5	7	(US-20050040472-\$).did. or (US-6515340-\$ or US-6515348-\$ or US-6087706-\$ or US-6040589-\$ or US-5191397-\$ or US-5113234-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/03/17 12:16
S6	742	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near5 (thick thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:17
S7	0	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near5 (thick thickness) near5 ".ANG.")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:18
S8	0	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 ".ANG.")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:18

S9	63	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 ("ANG." ".mu.m" Angstrom))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:29
S10	33	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 ("ANG." ".mu.m" Angstrom)) and (thick thickness). ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:31
S11	4	(thin adj film adj transistor tft).ti, ab,clm. and ((active adj (layer film) semiconductor adj thin adj film) near10 (thick thickness) near10 ("ANG." ".mu.m" Angstrom)) and (thick thickness) near4 active.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:15
S12	6	"665204".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:17
S13	1	InP near4 buffer and buffer near4 graded and graded near4 InGaAsP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:18
S14	3	InP near8 buffer and buffer near8 graded and graded near8 InGaAsP	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:19
S15	5	InP near16 buffer and buffer near16 graded and graded near16 InGaAsP and (photodiode photodetect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:20
S16	8	(US-20050040472-\$.did. or (US-5113234-\$ or US-5191397-\$ or US-6040589-\$ or US-6087706-\$ or US-6515340-\$ or US-6515348-\$.did. or (EP-235827-\$.did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:00

S17	148	(SiGe silicon adj germanium SiC silicon adj carbide) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 16:00
S18	67	(SiGe silicon adj germanium and SiC silicon adj carbide) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:12
S19	5	((SiGe silicon adj germanium) and (SiC silicon adj carbide)) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:15
S20	0	wo-0282526\$-\$.did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 15:15
S21	0	wo-0282526\$-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:15
S22	1	wo-200282526\$-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:17
S23	2	jp-2003046068\$-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 15:17
S24	43	(ONO silicon adj oxynitride) near6 substrate and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/17 16:05
S25	9	(US-20020014625-\$ or US-20050040472-\$).did. or (US-5113234-\$ or US-5191397-\$ or US-6040589-\$ or US-6087706-\$ or US-6515340-\$ or US-6515348-\$).did. or (EP-235827-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:01
S26	1	S25 and (buried adj oxide BOx)	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 09:02

S27	11	(buried adj oxide BOx) near6 insulating adj (layer film) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:17
S28	519	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:17
S29	179	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm.	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 09:19
S30	66	(buried adj oxide SIMOx) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm. and buried	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 10:31
S31	0	(buried adj oxide SIMOx) near3 (preferabl\$1 advantage) and ("SOI" silicon-on-insulator) and (thin adj film adj transistor tft).ti, ab,clm. and buried	US-PGPUB; USPAT; DERWENT	OR	ON	2005/03/18 10:32
S32	266	(buried adj oxide SIMOx) near12 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:32
S33	10	(buried adj oxide SIMOx) near12 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:42
S34	1	(buried adj oxide SIMOx) near12 (preferabl\$1 advantage) near12 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:47
S35	2	("6335231").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 10:45
S36	0	(buried adj oxide) near12 (preferabl\$1 advantage) near12 wafer adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48

S37	183	(buried adj oxide) near12 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S38	104	(buried adj oxide) near6 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S39	75	(buried adj oxide) near4 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S40	58	(buried adj oxide) near3 (preferabl\$1 advantage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S41	0	(buried adj oxide) near3 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:48
S42	2	(buried adj oxide) near6 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:49
S43	5	(buried adj oxide) near8 (preferabl\$1 advantage) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:51
S44	2283	pixel adj electrode near6 (contact\$3 connect\$3 abut\$4) near6 (insulating buried oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:52

S45	2045	pixel adj electrode near6 (contact\$3 connect\$3 abut\$4) near6 (insulating buried adj oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:52
S46	785	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:53
S47	669	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide) and thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S48	415	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating buried adj oxide dioxide) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S49	0	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (buried adj oxide) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:54
S50	467	pixel adj electrode near3 (contact contacting contacted connected connect connecting abut abutting) near3 (insulating adj (film layer)) and thin adj film adj transistor.ti, ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:55
S51	9	(US-20020014625-\$ or US-20050040472-\$).did. or (US-5113234-\$ or US-5191397-\$ or US-6040589-\$ or US-6087706-\$ or US-6515340-\$ or US-6515348-\$).did. or (EP-235827-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/18 11:33
S52	1	S51 and furuta.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 11:33

S53	1	S51 and furuta.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 14:20
S54	122	silicon adj oxynitride near3 dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 14:20
S55	68	silicon adj oxynitride near2 dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S56	3	("6040589").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39
S57	1	S56 and interconnect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 15:39